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Erratum: "Ion-channeling analysis of boron clusters in silicon" [J. Appl. Phys. 90, 4741 (2001)]

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The title of the paper should have been: "Ion channeling for strain analysis in buried nanofilms (<6 nm)." In addition, three references appeared incorrectly; corrected versions of Refs. 1, 7, and 13 follow:

¹B. D. Cullity, *Elements of X-Ray Diffraction* (Addison-Wesley, Reading, MA, 1976).

⁷T. C. Q. Noakes, P. Baily, P. K. Hucknall, K. Donovan, and M. A. Howson, *Phys. Rev. B* **58**, 4934 (1998).

¹³J. Lindhard and K. Dan., *Vidensk. Selsk. Mat. Fys. Medd.* **1965**, 34.

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